

PNP high-voltage transistor (PNP high-voltage transistor)

Manufacturers	<a href="#">NXP Semiconductor</a>
Package/Case	SOT-23
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for PMBT5401 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

PMBT5401 is a type of small-signal NPN transistor that is commonly used in low-power applications. It has a maximum collector current rating of 200 mA and a maximum collector-emitter voltage rating of 40 V. Some of its key features include:

### Features

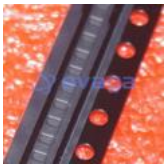
- High current gain (hFE) of up to 600 at a collector current of 10 mA
- Low base-emitter saturation voltage (VBEsat) of 0.7 V at a collector current of 10 mA
- Fast switching speed and low on-resistance

### Application

- Amplification of low-level signals in audio, radio, and other electronic circuits
- Switching small loads in digital circuits and low-power switching applications
- Voltage regulation and control in power management circuits
- Current amplification in sensor circuits



**Related Products**



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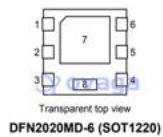
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